

EV182657403



MI22-1660
Micron Technology, Inc.

Dated: June 11, 2002

The stamp of the U.S. Patent and Trademark Office acknowledges receipt of the following papers relating to the Patent application of Belford T. Coursey, Serial No. 09/810,595, filed March 15, 2001, entitled "Memory Circuitry, and Dynamic Random Access Memory Circuitry (as amended)".

1. PTO Return Postcard Receipt;
2. A \$180 check;
3. Transmittal Form (PTO/SB/21) & Fee Transmittal (PTO/SB/17) in duplicate;
4. Supplemental information Disclosure Statement, Form 1449 & cited references.

EV077331732US

TECHNICAL STAMP
OCT 21 2003
OIP

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application Serial No. 09/810,595
 Filing Date March 15, 2001
 Inventor Belford T. Coursey
 Assignee Micron Technology, Inc.
 Group Art Unit 2813
 Examiner Y. Huynh
 Attorney's Docket No. MI22-1660
 Title: Memory Circuitry, and Dynamic Random Access Memory Circuitry

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

References - See Attached Form PTO-1449

Dear Sir:

The Examiner's attention is directed to the references which are listed on the attached Form PTO-1449 and copies of which are attached.

Citation of these references is respectfully requested.

A check in the amount of \$180 is enclosed to cover the fee specified under 37 C.F.R. § 1.17(p).

Respectfully submitted,

Dated: 6/6/02By: [Signature]

Mark S. Matkin
Reg. No. 32,268

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Sheet 1 of 1

Form PTO-1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
M132-1660SERIAL NO.
09-810,955PATENT CITATION APPLICANT
(If not, leave blank; if necessary,)APPLICANT
Belford T. CourseyFILING DATE
March 15, 2001GROUPO
2613

U.S. PATENT DOCUMENTS

*Examination Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
4/6	AA 6,057,206	05/2000	Nguyen et al.	438/	401	
	AC 6,130,126	09/2000	Iwakiri	438/	253	
	AD 6,232,168	05/2001	Coursey	438/	241	
	AE 6,030,879	02/2000	Huang et al.	438/	397	
	AF 4,996,627	02/1991	Zias et al.	361/	283	
	AG 5,770,499	06/1998	Kwok et al.	438/	253	
	AH 6,218,729	07/2001	DeBoer et al.	438/	745	
	AI 5,990,021	11/1999	Prahl et al.	438/	745	
	AJ 6,200,898	03/2001	Tu	438/	692	
	AK 6,232,210	05/2001	Tung	438/	745	
	AL 6,054,394	04/2000	Wang	438/	753	

FOREIGN PATENT DOCUMENTS

	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
	AM						
	AN						
	AO						
	AP						
	AO						

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

	AR	E. Fujii, et al., "ULSI DRAM Technology with $Ba_2Si_4TiO_5$ Film of 1.3nm Equivalent SiO_2 Thickness and $10^{-8} A/cm^2$ Leakage Current" IEEE 1992, IEDM 92-257 - 270
	AS	
	AT	

EXAMINER

DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

→ INS was 10/01/01 and was refiled on 6/25/02